Contribution ID: **487** Type: **Poster Presentation**

Diffusion studies of Xenon and Krypton implanted in CVD-SiC

Thursday, 12 July 2012 17:30 (2 hours)

Abstract content
   (Max 300 words)

The diffusion behaviour of implanted xenon and Krypton in CVD-SiC has been investigated using Rutherford backscattering spectroscopy (RBS) and Scanning electron microscopy (SEM) techniques. Xenon (Xe+) and Krypton ions with an energy of 360 KeV were implanted in SiC to a fluence of 2 × 10¹⁶ cm⁻² at room temperature (23℃), 350℃ and 600℃. Sequential annealing was performed from 1000℃ to 1500℃ in 100℃. By comparing the widths of the as implanted profiles to the after annealing profiles the diffusion coefficients was determined while the changes in samples surfaces were monitored by SEM.

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no

Level for award
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na

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no

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Session Classification: Poster Session

Track Classification: Track A - Division for Condensed Matter Physics and Materials